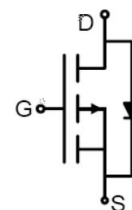
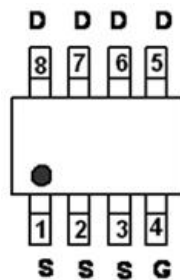
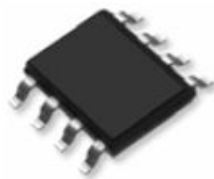


V_{DSS}	-150V
$R_{DS(on)}$	265m (typ.)
I_D	-2A

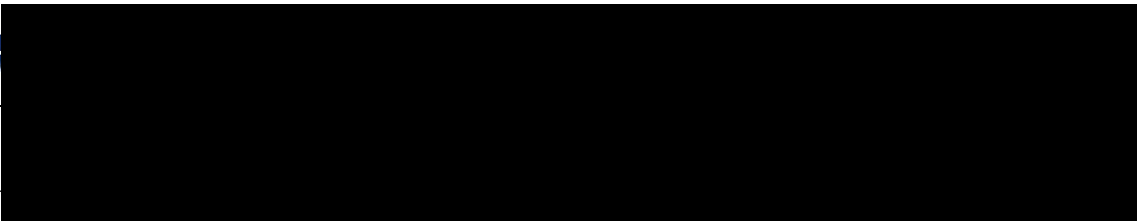


Advanced MOSFET process technology
 Special designed for PWM, load switching and
 general purpose applications
 Ultra low on-resistance with low gate charge
 Fast switching and reverse body recovery
 150 °C operating temperature



It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current	-2	A
$I_D @ T_A = 100^\circ\text{C}$	Continuous Drain Current	-1.4	
I_{DM}	Pulsed Drain Current	-8	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation	3	W
V_{DS}	Drain-Source Voltage	-150	V
V_{GS}	Gate-to-Source Voltage	± 20	V
$T_J \quad T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

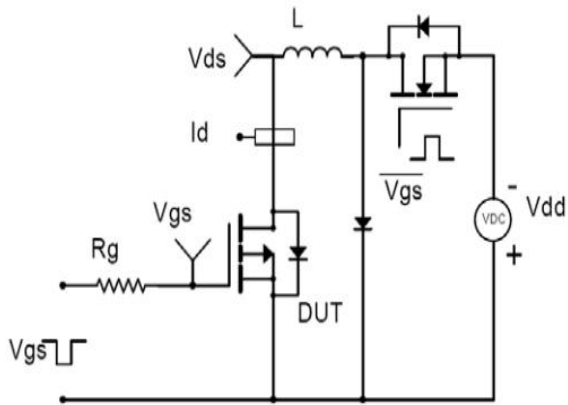


R _{JA}	Junction-to-ambient ()	—	42	°C/W
-----------------	-------------------------	---	----	------

@T_J=25°C unless otherwise specified

V _{(BR)DSS}	Drain-to-Source breakdown voltage	-150	—	V	V _{GS} = 0V, I _D = -250μA
V _{GS(on)}	Gate threshold voltage	265	345	mV	V _{GS} =-10V, I _D = -2A
V _{GS(th)}	Gate threshold voltage	-2	-4	V	V _{DS} = V _{GS} , I _D = -250μA
I _{DS(on)}	Drain-to-Source leakage current	—	-1	μA	V _{DS} = -150V, V _{GS} = 0V
I _{GS(on)}	Gate forward leakage current	—	100	nA	V _{GS} = 20V
I _{GS(off)}	Gate reverse leakage current	—	100	nA	V _{GS} = -20V
Q _{tot}	Total gate charge	—	38	—	I _D = -2A,
Q _g	Gate-to-source charge	—	8	nC	V _{DS} =-50V,
Q _{gd}	Gate-to-drain ("Miller") charge	—	9	—	V _{GS} = -10V
t _{d(on)}	Turn-On delay time	—	31	—	
t _r	Rise time	—	33	—	V _{GS} =-10V, V _{DS} =-50V,
t _{d(off)}	Turn-Off delay time	—	240	—	R _{GEN} =3 Ω, R _L =25 Ω
t _f	Fall time	—	130	—	
L _s	Source inductance	—	—	—	



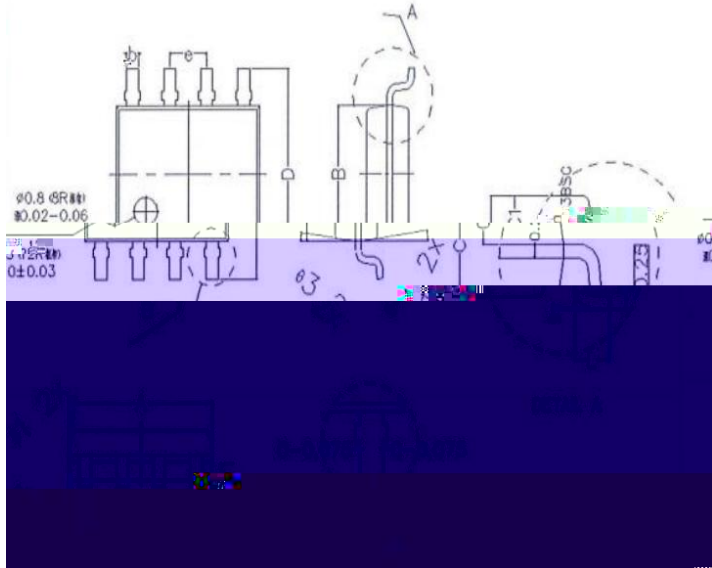


Calculated continuous current based on maximum allowable junction temperature.

Repetitive rating; pulse width limited by max. junction temperature.

The power dissipation P_D is based on max. junction temperature, using junction-to-case thermal resistance.

The value of R_{JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$



COMMON DIMENSIONS (UNITS OF MEASURE 15 mm)			
	MIN	NORMAL	MAX
A	4.800	4.900	5.000
B	3.800	3.900	4.000
C	1.350	1.450	1.550
C1	0.650	0.700	0.750
D	5.950	6.120	6.280
L	0.500	0.600	0.700
b	0.350	0.400	0.450
h	0.070	0.150	0.250
e	1.270TYPE		
θ ₁	7° TYPE(8P)		



Any and all Silikron products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems,
